



10A, 650V N-CHANNEL POWER MOSFET

DESCRIPTION

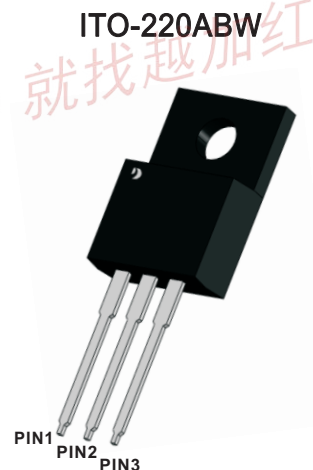
The F10N65 is a high voltage power MOSFET combines advanced trench MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications of switching power supplies and adaptors.

Features

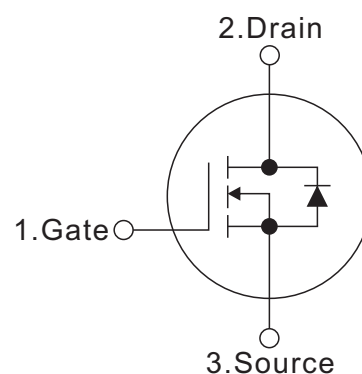
- $R_{DS(ON)} \leq 1.0 \Omega @ V_{GS}=10V, I_D=5.0A$
- Fast switching capability
- Avalanche energy tested
- Improved dv/dt capability, high ruggedness

Mechanical data

- Case: ITO-220ABW
- Approx. Weight: 2.1g (0.07oz)
- Lead free finish, RoHS compliant
- Case Material: "Green" molding compound, UL flammability classification 94V-0, "Halogen-free".



SYMBOL



ABSOLUTE MAXIMUM RATINGS (TA=25°C, unless otherwise specified)

PARAMETER	Symbols	RATINGS	Units
Drain-Source Voltage	V_{DSS}	650	V
Gate-Source Voltage	V_{GSS}	± 30	V
Continuous Drain Current	I_D	10	A
Pulsed Drain Current (Note 2)	I_{DM}	20	A
Avalanche Energy Single Pulsed (Note 3)	E_{AS}	800	mJ
Peak Diode Recovery dv/dt (Note 4)	dv/dt	2.1	V/ns
Power Dissipation	P_D	38	W
Operation Junction Temperature and Storage Temperature	T_j, T_{stg}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. L = 100mH, IAS = 4.1A, VDD = 50V, RG = 25 Ω , Starting TJ = 25°C

4. ISD \leq 10A, di/dt \leq 200A/ μ s, VDD \leq BVDSS, Starting TJ = 25°C

THERMAL DATA

PARAMETER	Symbols	RATINGS	Units
Junction to Ambient	R_{thJA}	63	V
Junction to Case	R_{thJC}	4	V

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.



ELECTRICAL CHARACTERISTICS (TA=25°C, unless otherwise specified)

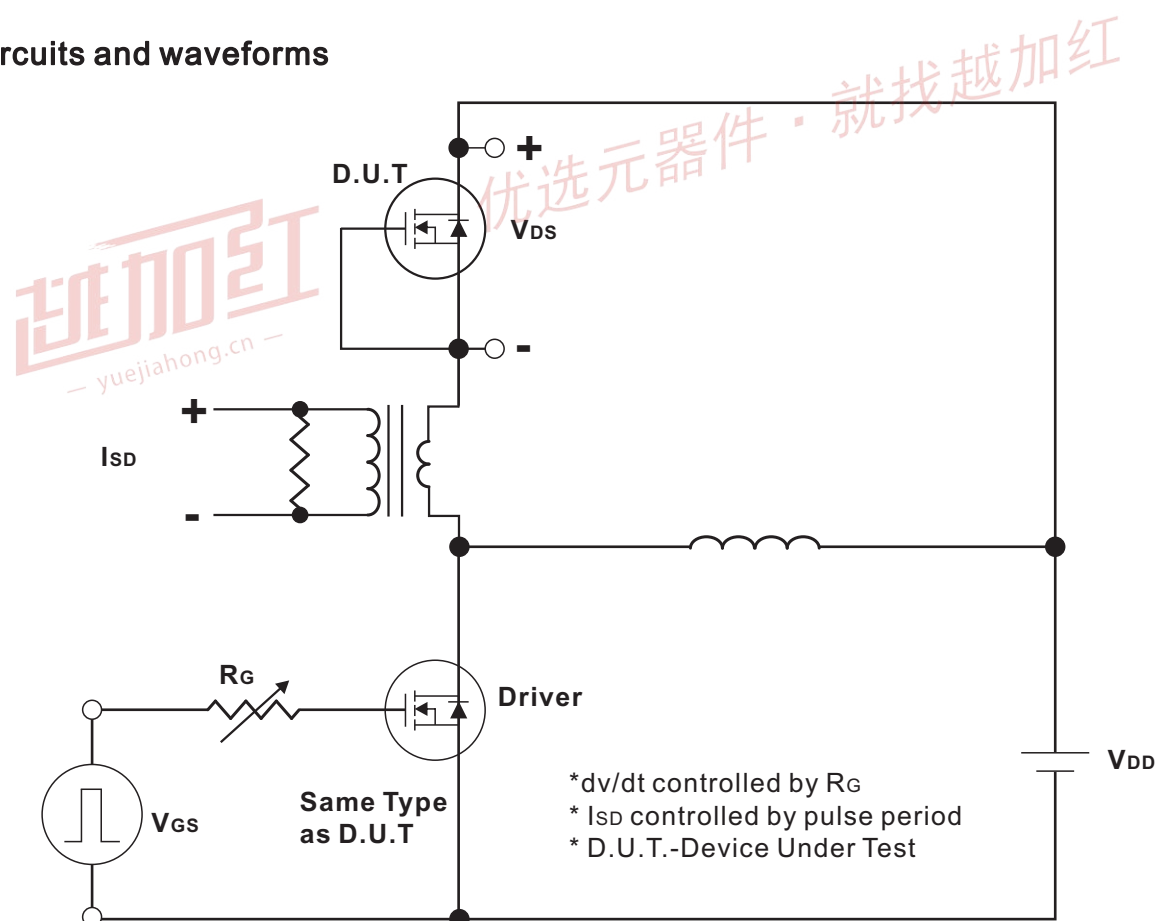
PARAMETER	Symbols	TEST CONDITIONS	Min	Typ	Max	Units
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{DS}=0V, I_D=250\mu A$	650			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=650V, V_{GS}=0V$			10	μA
Gate- Source Leakage Current	Forward	I_{GSS}			100	nA
	Reverse					
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=5.0A$			1.0	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{DS}=25V,$ $V_{GS}=0V,$ $f=1.0MHz$		1530		pF
Output Capacitance	C_{OSS}			130		pF
Reverse Transfer Capacitance	C_{RSS}			5		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q_G	$V_{DS}=520V, V_{GS}=10V,$ $I_D=10A, I_G=1mA$ (NOTE1,2)		31		nC
Gate-Source Charge	Q_{GS}			7.6		nC
Gate-Drain Charge	Q_{GD}			5.8		nC
Turn-On Delay Time (Note 1)	$t_{D(ON)}$	$V_{DS}=100V, V_{GS}=10V,$ $I_D=10A, R_G=25\Omega$ (NOTE1,2)		20		ns
Turn-On Rise Time	t_R			21		ns
Turn-Off Delay Time	$t_{D(OFF)}$			98		ns
Turn-Off Fall Time	t_F			35		ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Maximum Body-Diode Continuous Current	I_S				10	A
Maximum Body-Diode Pulsed Current	I_{SM}				20	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	$I_S=10A, V_{GS}=0V$			1.4	V
Reverse Recovery Time (Note 1)	t_{rr}	$I_S=10A, V_{GS}=0V,$ $di/dt=100A/us$		376		ns
Reverse Recovery Charge	Q_{rr}			8.5		μC

Notes:

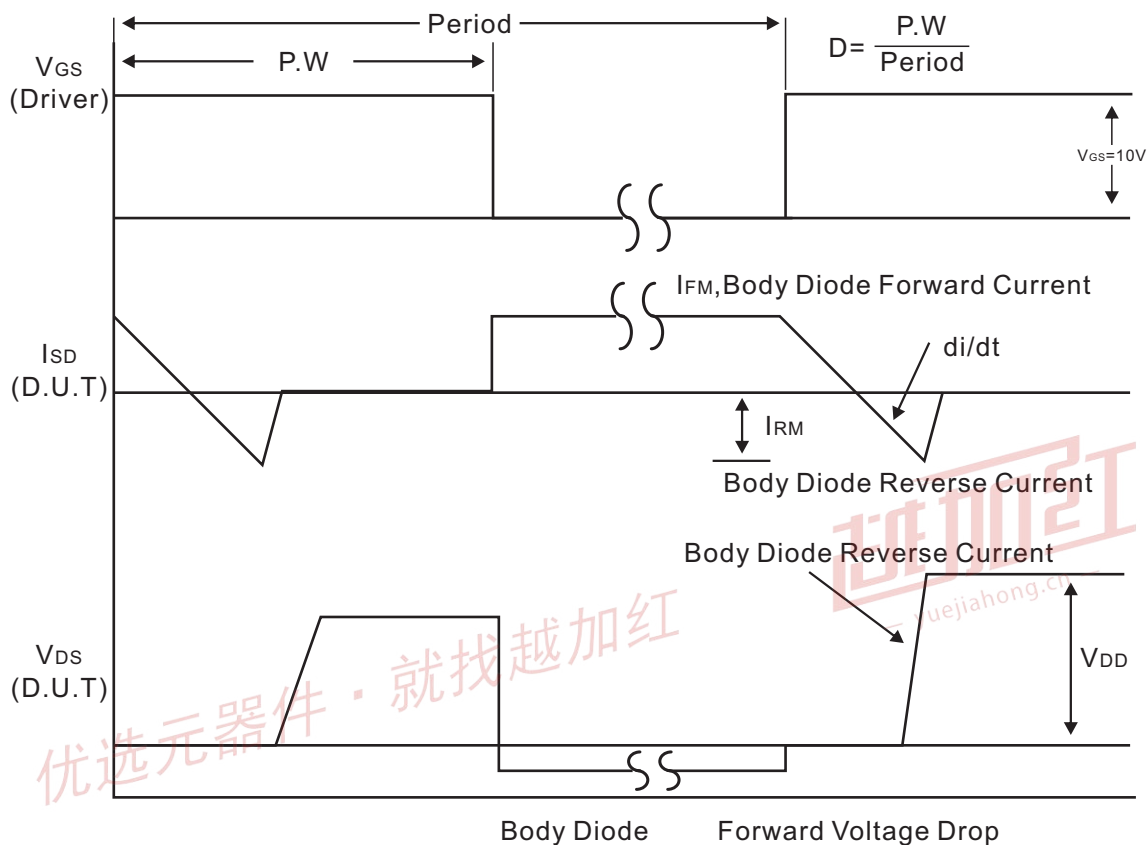
1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.
2. Essentially independent of operating temperature.



Test Circuits and waveforms



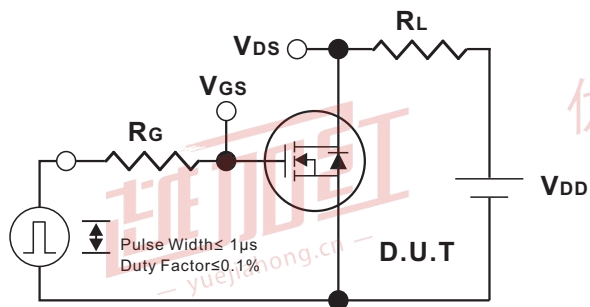
Peak Diode Recovery dv/dt Test Circuit



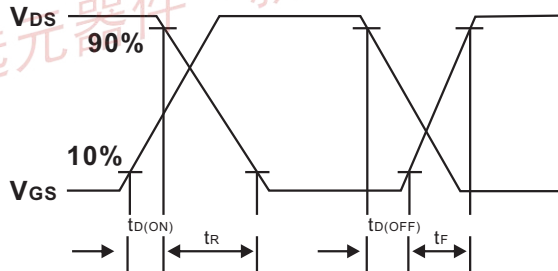
Peak Diode Recovery dv/dt Waveforms



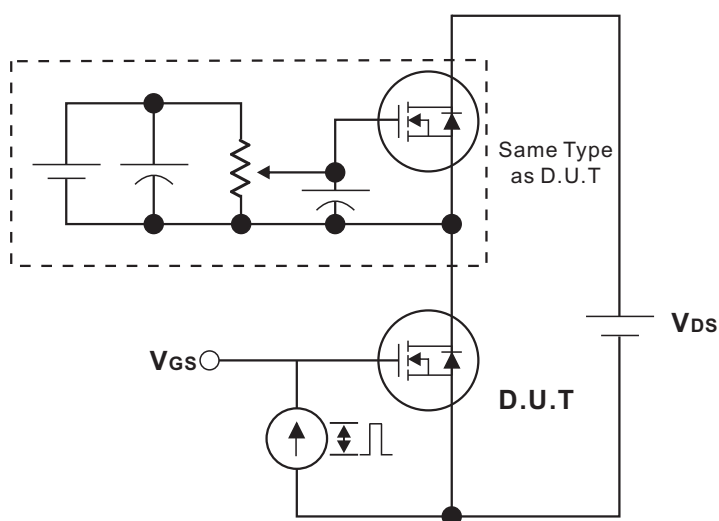
Test Circuits and waveforms



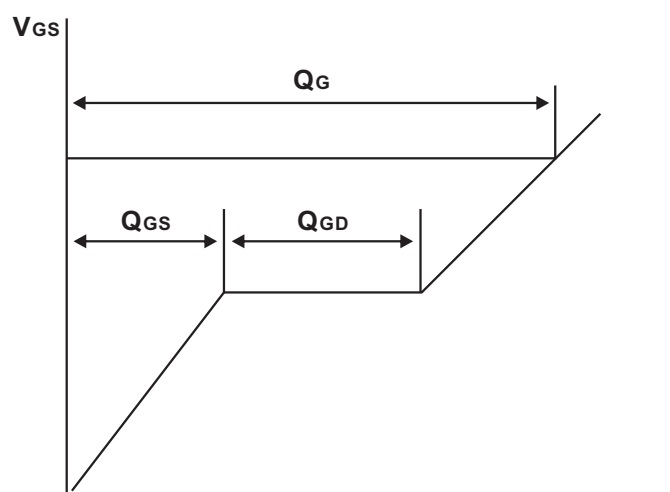
Switching Test Circuit



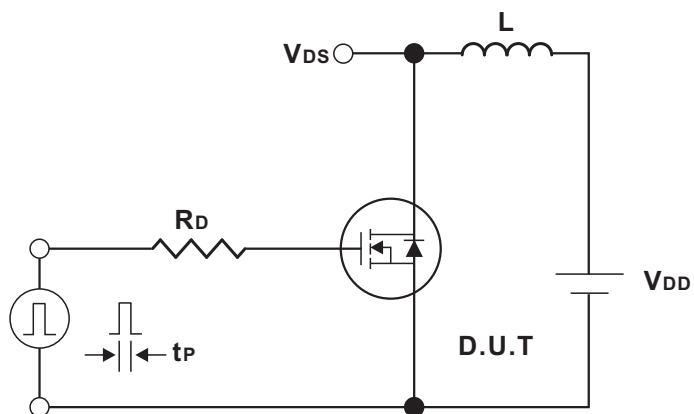
Switching Waveforms



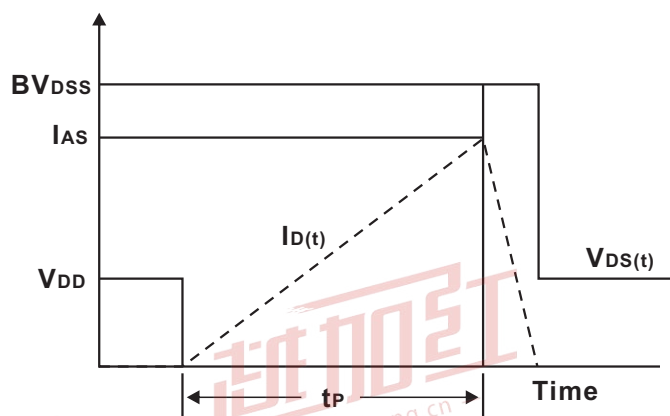
Gate Charge Test Circuit



Charge
Gate Charge Waveform



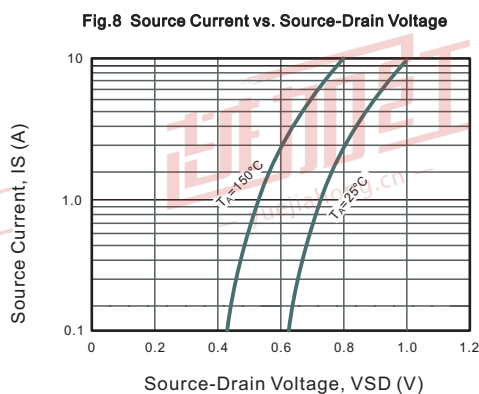
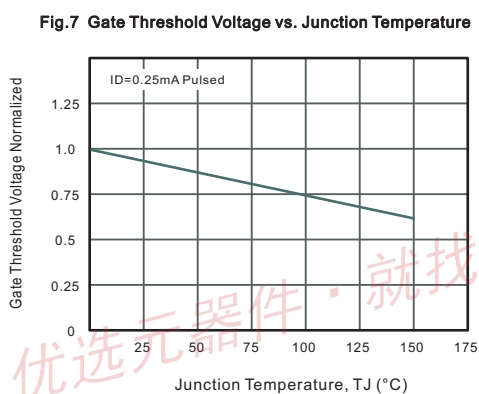
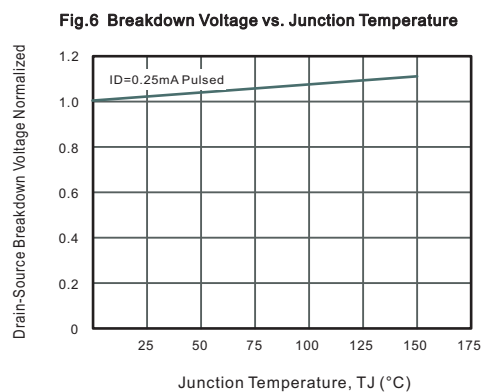
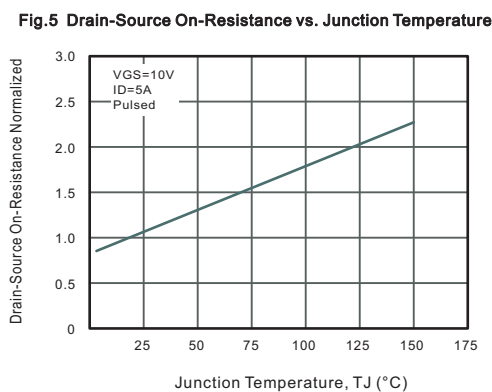
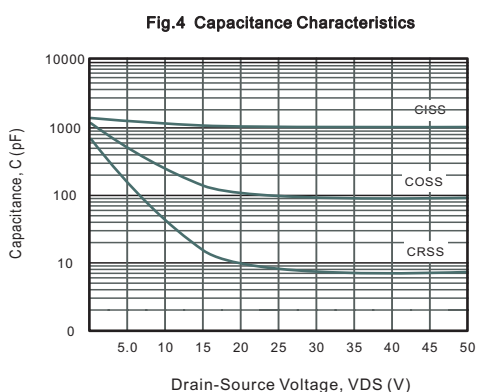
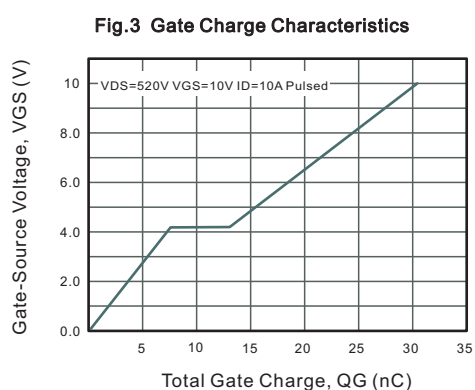
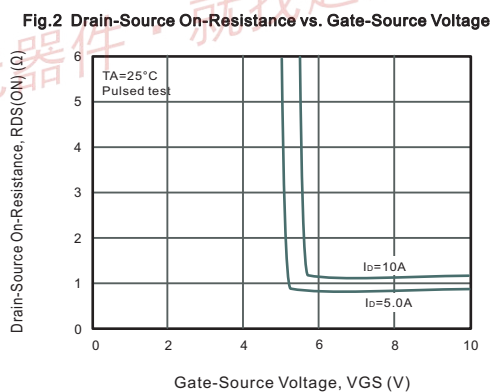
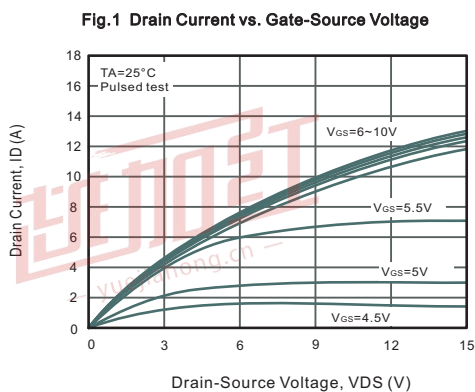
Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

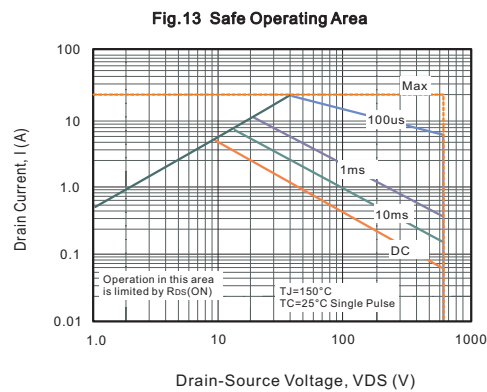
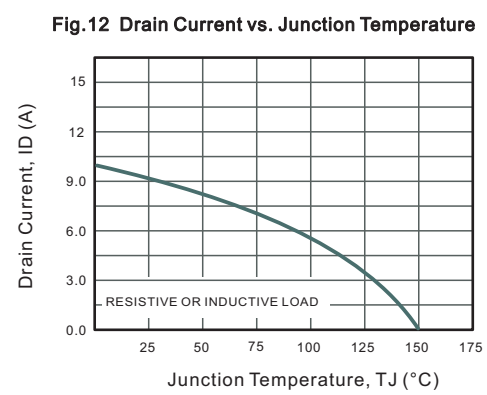
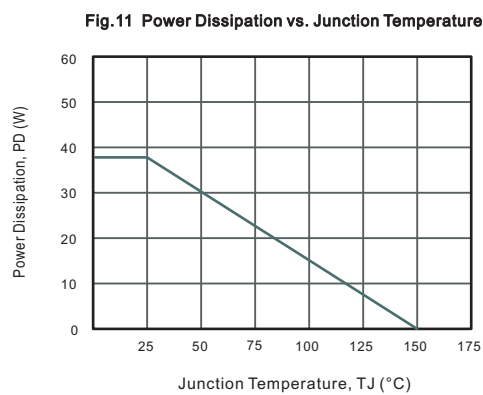
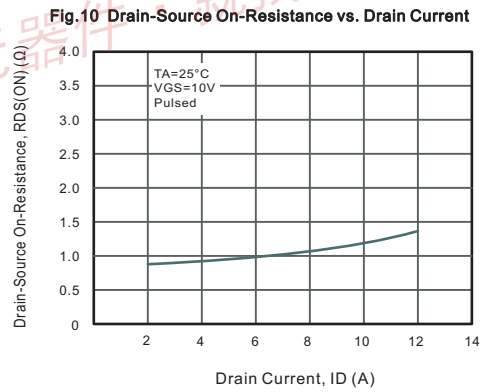
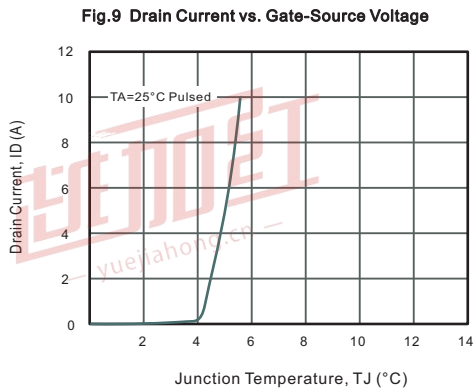


Typical Characteristics





Typical Characteristics



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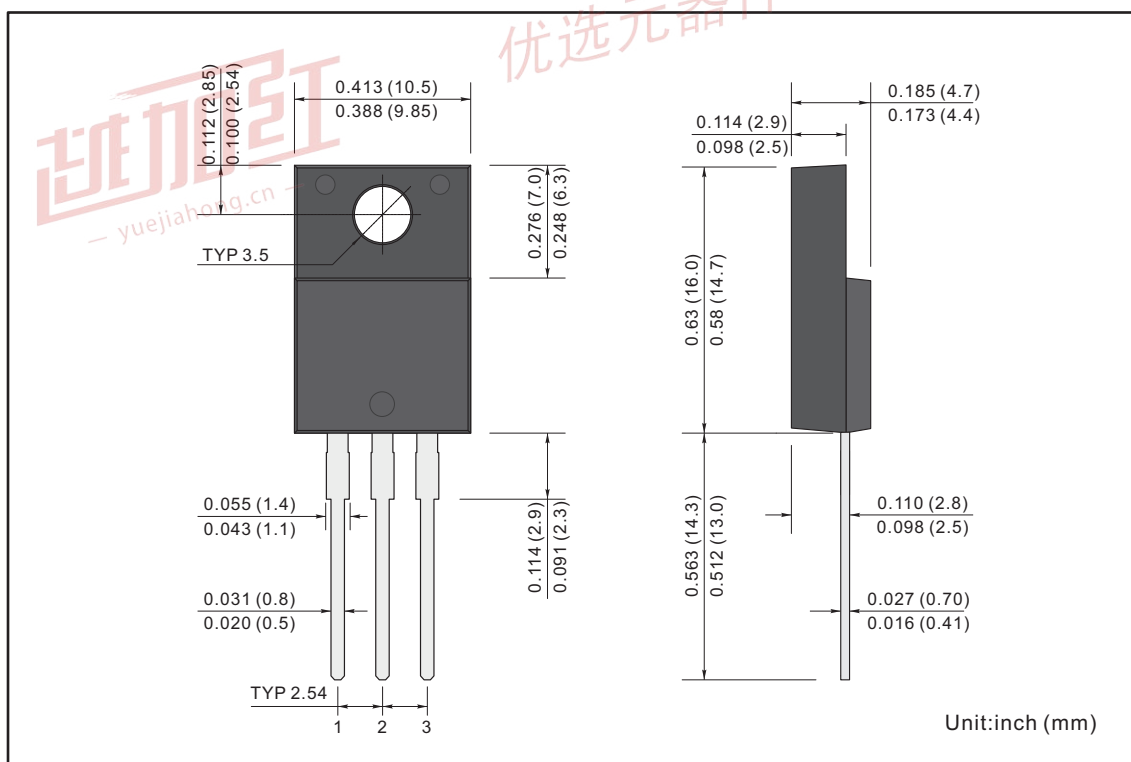
越加红
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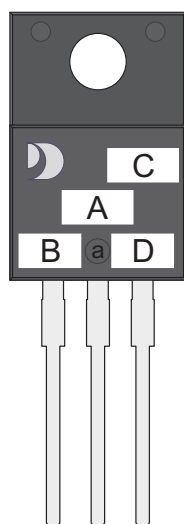
PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

ITO-220ABW



MARKING DIAGRAM



- Unmarkable Surface
- Marking Composition Field
- a: Ejector Pin Mark
- A: Marking Area
- B: Lot Code
- C: Additional Information
- D: Date Code (YWW)
- Y: Years(0~9)
- WW: Week

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